Product data sheet

### 1. Product profile

### 1.1 General description

Planar passivated high commutation three quadrant triac in a SOT428 plastic package. This "series F" triac balances the requirements of commutation performance and gate sensitivity. The "less sensitive gate" "series F" is intended for interfacing with low power drivers, including microcontrollers in higher "noise" environments.

#### 1.2 Features and benefits

- 3Q technology for improved noise immunity
- Good immunity to false turn-on by dV/dt
- High commutation capability with less sensitive gate
- High voltage capability

- Less sensitive gate suitable for higher "noise" environment applications
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in three quadrants only

### 1.3 Applications

■ Electronic thermostats

General purpose motor controls

#### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol              | Parameter                            | Conditions  | Min | Тур | Max | Unit |
|---------------------|--------------------------------------|---|-----|-----|-----|------|
| $V_{DRM}$           | repetitive peak off-state voltage    |   | -   | -   | 800 | V    |
| I <sub>TSM</sub>    | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ;<br>$t_p = 20 \text{ ms}$ ; see Figure 4;<br>see Figure 5                  | -   | -   | 65  | Α    |
| I <sub>T(RMS)</sub> | RMS on-state current                 | full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$ ;<br>see <u>Figure 1</u> ; see <u>Figure 2</u> ;<br>see <u>Figure 3</u> | -   | -   | 8   | Α    |



Table 1. Quick reference data ...continued

| Symbol          | Parameter            | Conditions  | Min | Тур | Max | Unit |
|-----------------|----------------------|---|-----|-----|-----|------|
| Static char     | acteristics          |   |     |     |     |      |
| I <sub>GT</sub> | gate trigger current | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$<br>$T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$                       | -   | -   | 25  | mA   |
|                 |                      | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$<br>$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$          | -   | -   | 25  | mA   |
|                 |                      | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;} $<br>$T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ or } T_j}$ | -   | -   | 25  | mA   |

# 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                                 | Simplified outline | Graphic symbol |
|-----|--------|---|--------------------|----------------|
| 1   | T1     | main terminal 1                             |                    | <b>.</b> .     |
| 2   | T2     | main terminal 2[1]                          | mb                 | T2T1           |
| 3   | G      | gate  |                    | `G<br>sym051   |
| mb  | T2     | mounting base; connected to main terminal 2 | 1 3                |                |
|     |        |   | SOT428 (DPAK)      |                |

<sup>[1]</sup> it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package

# 3. Ordering information

Table 3. Ordering information

| Type number  | Package |   |         |
|--------------|---------|---|---------|
|              | Name    | Description   | Version |
| BTA208S-800F | DPAK    | plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped) | SOT428  |

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

|                     |                                      | ,   |     |     |                  |
|---------------------|--------------------------------------|---|-----|-----|------------------|
| Symbol              | Parameter                            | Conditions  | Min | Max | Unit             |
| $V_{DRM}$           | repetitive peak off-state voltage    |   | -   | 800 | V                |
| I <sub>T(RMS)</sub> | RMS on-state current                 | full sine wave; $T_{mb} \le 102 \text{ °C}$ ; see Figure 1;<br>see Figure 2; see Figure 3   | -   | 8   | Α                |
| I <sub>TSM</sub>    | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25  ^{\circ}C$ ; $t_p = 20  ms$ ; see Figure 4; see Figure 5 | -   | 65  | Α                |
|                     |                                      | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$                     | -   | 71  | Α                |
| I <sup>2</sup> t    | I <sup>2</sup> t for fusing          | $t_p = 10 \text{ ms}$ ; sine-wave pulse   | -   | 21  | A <sup>2</sup> s |
| dI <sub>T</sub> /dt | rate of rise of on-state current     | $I_T = 12 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$              | -   | 100 | A/μs             |
| I <sub>GM</sub>     | peak gate current                    |   | -   | 2   | Α                |
| $V_{GM}$            | peak gate voltage                    |   | -   | 5   | V                |
| $P_{GM}$            | peak gate power                      |   | -   | 5   | W                |
| P <sub>G(AV)</sub>  | average gate power                   | over any 20 ms period   | -   | 0.5 | W                |
| T <sub>stg</sub>    | storage temperature                  |   | -40 | 150 | °C               |
| T <sub>j</sub>      | junction temperature                 |   | -   | 125 | °C               |
|                     |                                      |   |     |     |                  |

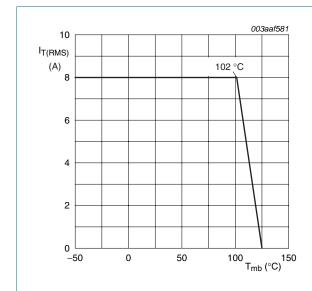


Fig 1. RMS on-state current as a function of heatsink temperature; maximum values

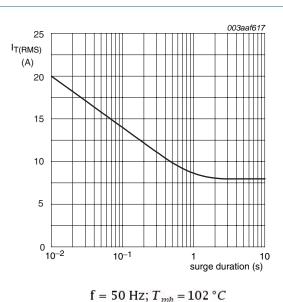


Fig 2. RMS on-state current as a function of surge

duration; maximum value

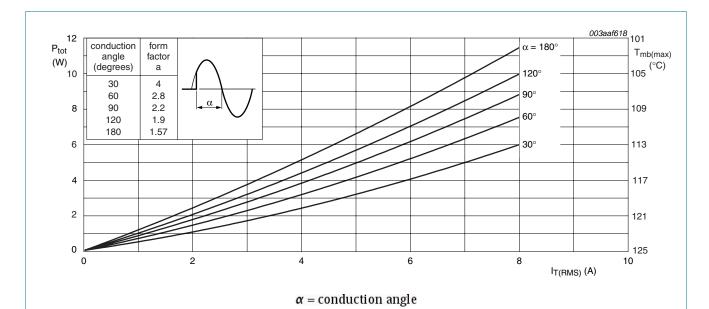


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

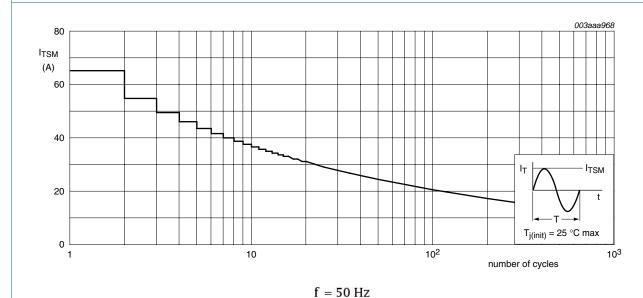
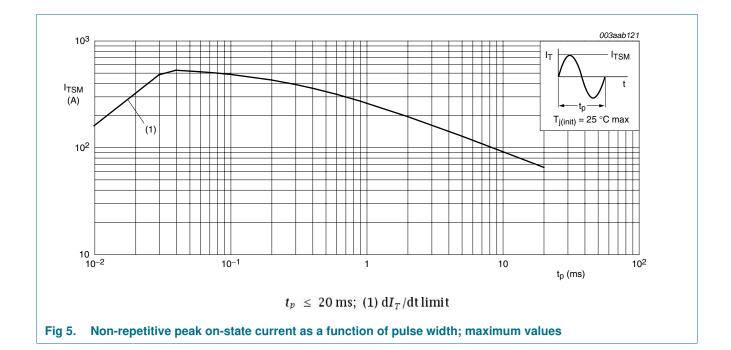


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter   | Conditions                                       | Min | Тур | Max | Unit |
|----------------|---|--|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | full cycle; see Figure 6                         | -   | -   | 2   | K/W  |
|                |   | half cycle; see Figure 6                         | -   | -   | 2.4 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | in free air; printed circuit board (FR4) mounted | -   | 75  | -   | K/W  |

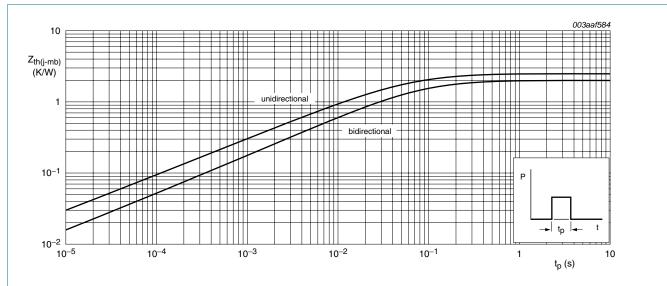
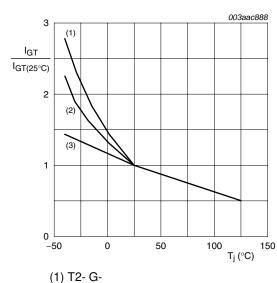


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse width

## 6. Characteristics

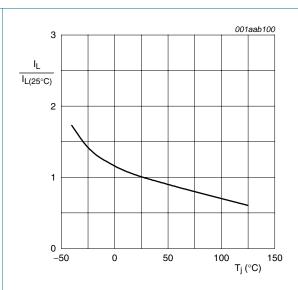
Table 6. Characteristics

| A                               | D                                     | O Put  |      | -   |      |      |
|---------------------------------|---------------------------------------|--|------|-----|------|------|
| Symbol                          | Parameter                             | Conditions   | Min  | Тур | Max  | Unit |
| Static char                     | racteristics                          |  |      |     |      |      |
| I <sub>GT</sub>                 | gate trigger current                  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; T_j = 25 °C;$<br>see <u>Figure 7</u>   | -    | -   | 25   | mA   |
|                                 |                                       | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-; T_j = 25 ^{\circ}C;$<br>see Figure 7   | -    | -   | 25   | mA   |
|                                 |                                       | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{T2- G-}; T_j = 25 \text{ °C};$<br>see Figure 7   | -    | -   | 25   | mA   |
| I <sub>L</sub> latching current | latching current                      | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+; T_j = 25 °C;$<br>see <u>Figure 8</u>   | -    | -   | 30   | mA   |
|                                 |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-; T_j = 25 °C;$<br>see Figure 8  | -    | -   | 45   | mA   |
|                                 |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{T2- G-}; T_j = 25 \text{ °C};$<br>see <u>Figure 8</u>  | -    | -   | 30   | mA   |
| I <sub>H</sub>                  | holding current                       | $V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{}$   | -    | -   | 30   | mΑ   |
| $V_{T}$                         | on-state voltage                      | $I_T = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{\text{Figure } 10}$  | -    | 1.3 | 1.65 | ٧    |
| V <sub>GT</sub>                 | gate trigger voltage                  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$<br>see Figure 11   | -    | 0.7 | 1.5  | V    |
|                                 |                                       | $V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11  | 0.25 | 0.4 | -    | V    |
| I <sub>D</sub>                  | off-state current                     | $V_D = 800 \text{ V}; T_j = 125 ^{\circ}\text{C}$  | -    | 0.1 | 0.5  | mA   |
| Dynamic o                       | haracteristics                        |  |      |     |      |      |
| dV <sub>D</sub> /dt             | rate of rise of off-state voltage     | $V_{DM}$ = 536 V; $T_j$ = 110 °C; exponential waveform; gate open circuit  | 70   | -   | -    | V/µs |
| dl <sub>com</sub> /dt           | rate of change of commutating current | $V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 8 \text{ A};$ $dV_{com}/dt = 0.1 ^{\circ}\text{V}/\mu\text{s}; gate open circuit}$  | 20   | -   | -    | A/ms |
|                                 |                                       | $V_D = 400 \text{ V}$ ; $T_j = 125 ^{\circ}\text{C}$ ; $I_{T(RMS)} = 8 \text{ A}$ ; $dV_{com}/dt = 10  V/\mu s$ ; gate open circuit; see Figure 12 | 14   | -   | -    | A/ms |

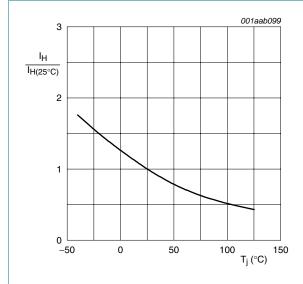


- (2) T2+ G-
- (3) T2+ G+

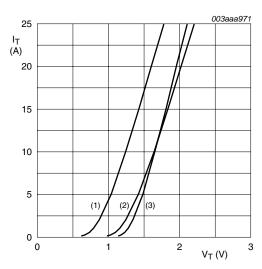
Normalized gate trigger current as a function of Fig 7. junction temperature



Normalized latching current as a function of Fig 8. junction temperature



Normalized holding current as a function of Fig 9. junction temperature



Vo = 1.264 V; Rs = 0.0378  $\Omega$ 

- (1) Tj = 125 °C; typical values
- (2) Tj = 125 °C; maximum values
- (3) Tj = 25 °C; maximum values

Fig 10. On-state current as a function of on-state voltage

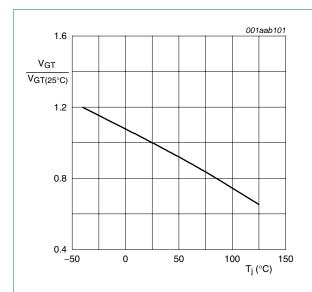


Fig 11. Normalized gate trigger voltage as a function of junction temperature

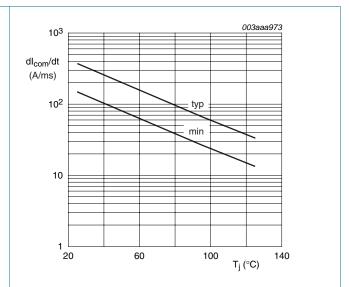


Fig 12. Rate of change of commutating current as a function of junction temperature; typical and minimum values

## 7. Package outline

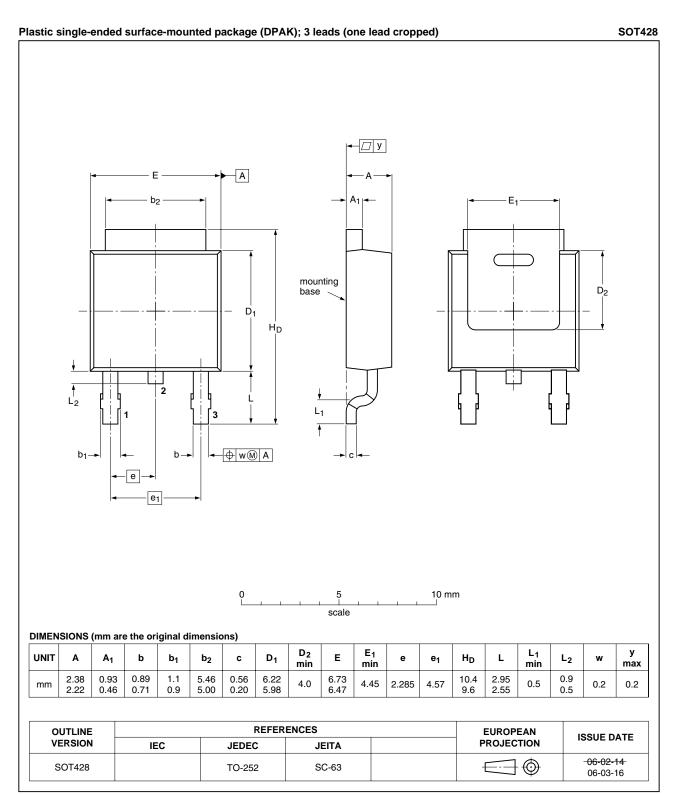
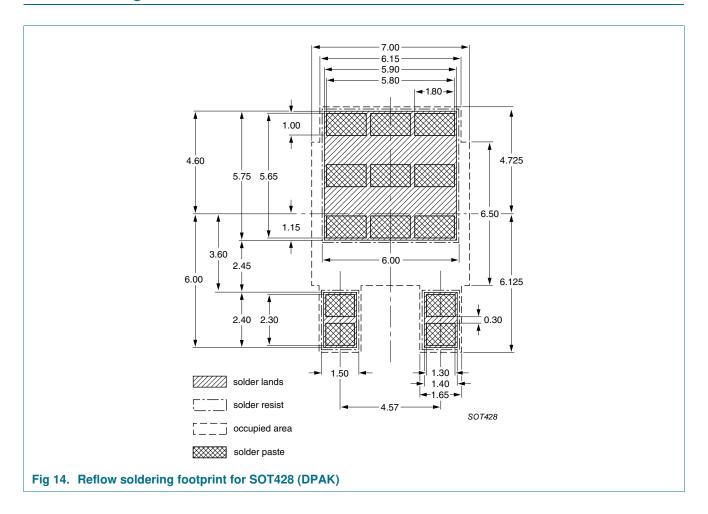


Fig 13. Package outline SOT428 (DPAK)

# 8. Soldering



# 9. Revision history

### Table 7. Revision history

| Document ID      | Release date                           | Data sheet status  | Change notice | Supersedes               |
|------------------|--|--------------------|---------------|--------------------------|
| BTA208S-800F v.6 | 20110414                               | Product data sheet | -             | BTA208S-800F v.5         |
| Modifications:   | <ul> <li>Various changes to</li> </ul> | o content.         |               |                          |
| BTA208S-800F v.5 | 20101123                               | Product data sheet | -             | BTA208S_SERIES_D_E_F v.4 |

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| Document status [1] [2]        | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

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- [2] The term 'short data sheet' is explained in section "Definitions".
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